

# SN55551, SN55552 ELECTROLUMINESCENT ROW DRIVER

D2743, APRIL 1986

- Each Device Drives 32 Electrodes
- High-Voltage Open-Drain DMOS Outputs
- 50-mA Output Current Capability
- CMOS-Compatible Inputs
- Very Low Steady-State Power Consumption

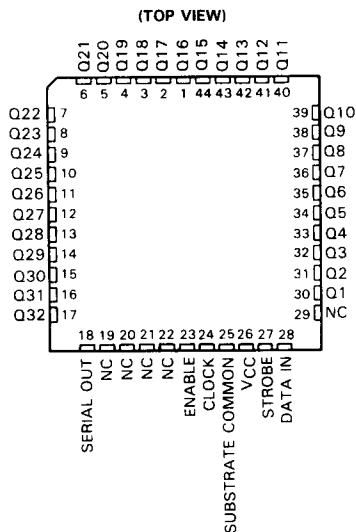
## description

The SN55551 and SN55552 are monolithic BIFET<sup>†</sup> integrated circuits designed to drive the row electrodes of an electroluminescent display. All inputs are CMOS-compatible and all outputs are high-voltage open-drain DMOS transistors. The SN55552 output sequence has been reversed from the SN55551 for ease in printed circuit board layout.

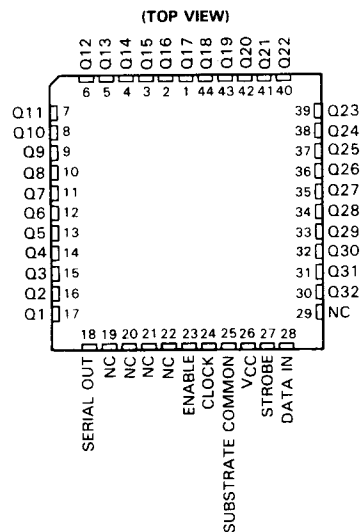
The devices consist of a 32-bit shift register, 32 AND gates, and 32 output OR gates. Typically, a composite row drive signal is externally generated by a high-voltage switching circuit and applied to the Substrate Common terminal. Serial data is entered into the shift register on the high-to-low transition of the clock input. A high Enable input allows those outputs with a high in their associated register to be turned on causing the corresponding row to be connected to the composite row drive signal. When the Strobe input is low, all output transistors are turned on. The Serial Data output from the shift register may be used to cascade additional devices. This output is not affected by the Enable or Strobe inputs.

The SN55551 and SN55552 are characterized for operation over the full military temperature range of -55°C to 125°C.

SN55551 . . . FD PACKAGE



SN55552 . . . FD PACKAGE



NC—No internal connection

<sup>†</sup> BIFET — Bipolar, double-diffused, N-channel and P-channel MOS transistors on same chip — patented process.

PRODUCTION DATA documents contain information current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

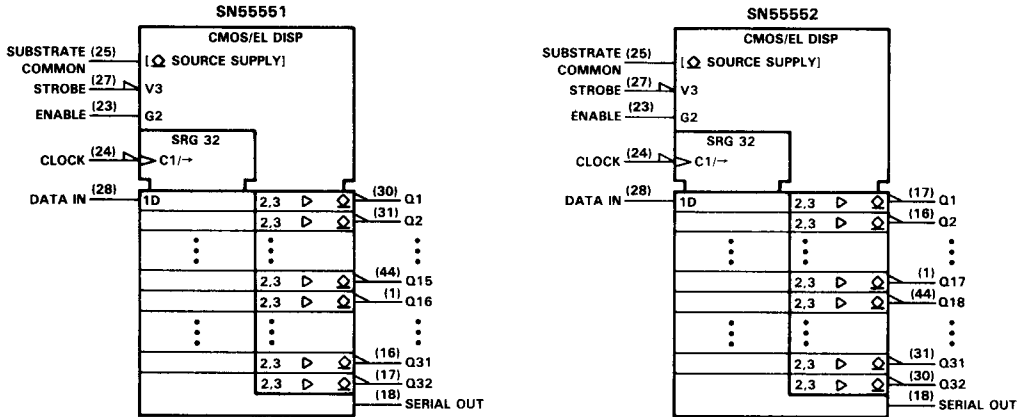
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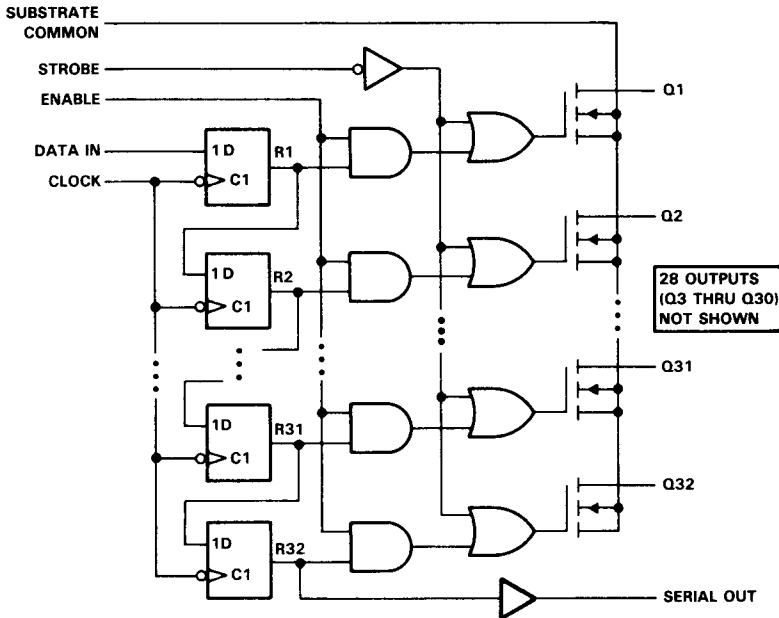
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logic symbols†



† These symbols are in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12. The symbol  here indicates an n-channel open-drain output.

logic diagram (positive logic)



# SN55551, SN55552 ELECTROLUMINESCENT ROW DRIVER

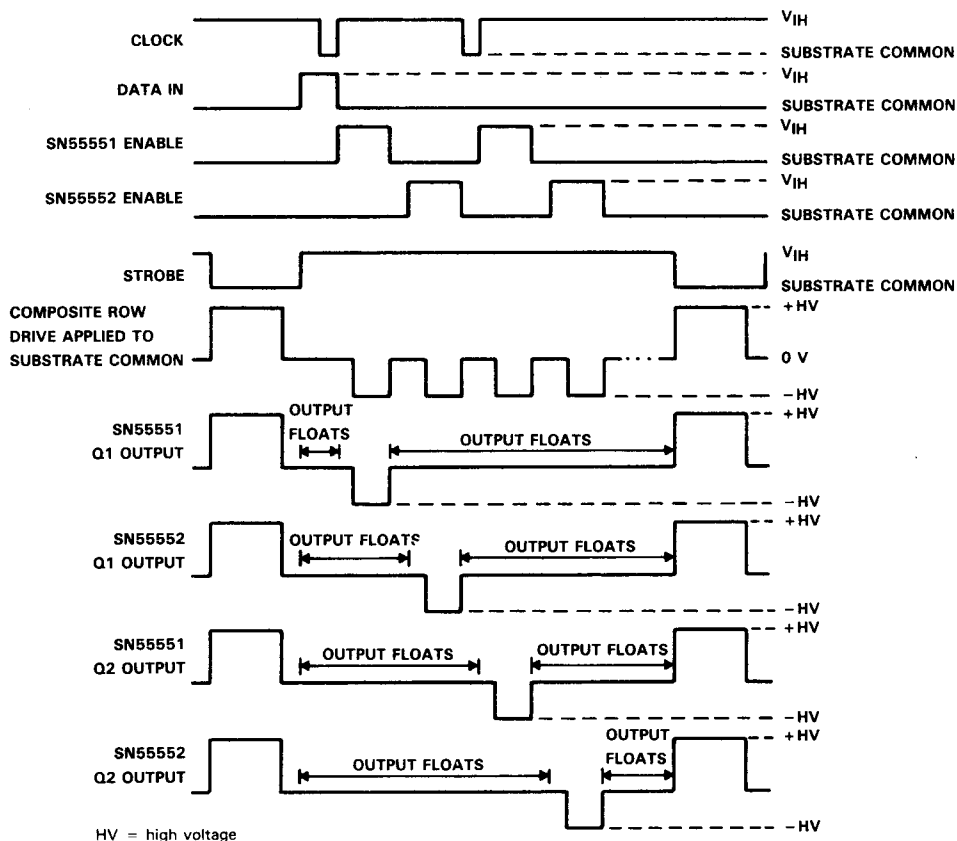
FUNCTION TABLE

FUNCTION	CONTROL INPUTS			SHIFT REGISTERS R1 THRU R32	OUTPUTS	
	CLOCK	ENABLE	STROBE		SERIAL	Q1 THRU Q32
LOAD	↓	X	X	Load and Shift†	R32	Determined by Enable and Strobe
	No. ↓	X	X	No Change	R32	Determined by Enable and Strobe
ENABLE	X	L	H	As determined above	R32	All Q outputs off
	X	H	H	As determined above	R32	Determined by R1 through R32
STROBE	X	X	L	As determined above	R32	All Q outputs on

H = high level, L = low level, X = irrelevant, ↓ = high-to-low transition.

†Register R32 takes on the state of R31, R31 takes on the state of R30, . . . R2 takes on the state of R1, and R1 takes on the state of the data input.

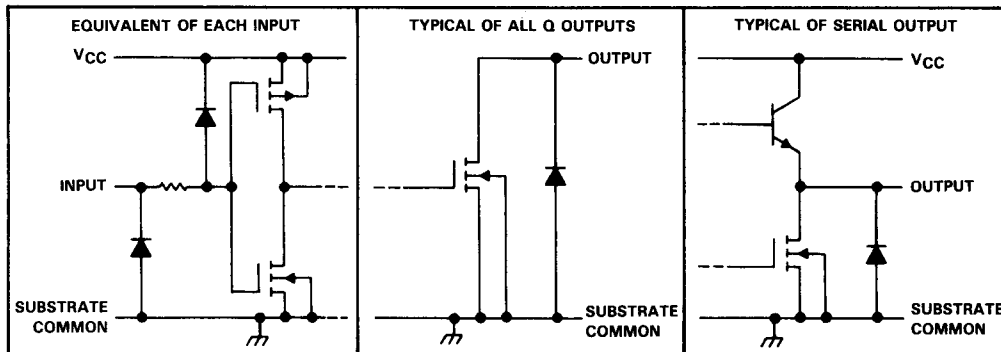
## typical operating sequence



NOTE: During operation Clock, Data In, Enable, and Strobe are referenced to the Composite Row Drive signal received at the Substrate Common pin of the device.

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## schematic of inputs and outputs



## absolute maximum ratings over operating temperature range (unless otherwise noted)

Supply voltage, $V_{CC}$ (see Note 1)	18 V
Q off-state output voltage, $V_{O(off)}$	225 V
Input voltage	$V_{CC} + 0.3$ V
Substrate common terminal current (see Note 2)	1.5 A
Continuous total dissipation at (or below) 25°C free-air temperature (see Note 3)	1825 mW
Minimum operating free-air temperature	-55°C
Operating case temperature	125°C
Storage temperature range	-65°C to 150°C
Case temperature for 60 seconds	260°C

- NOTES: 1. Voltage values are with respect to substrate common terminal.  
 2. Duty cycle is limited by package dissipation.  
 3. For operation above 25°C free-air temperature, derate linearly at the rate of 14.6 mW/°C.

## recommended operating conditions

		MIN	NOM	MAX	UNIT	
$V_{CC}$	Supply voltage	10.8	12	15	V	
$V_{O(off)}$	Off-state Q output voltage	0		200	V	
$V_{IH}$	High-level input voltage	$0.75V_{CC}$		$V_{CC} + 0.3$	V	
$V_{IL}$	Low-level input voltage	-0.3		$0.25V_{CC}$	V	
$I_{O(on)}$	On-state Q output current	$V_{DD} = 80$ V, Duty cycle $\leq 1\%$	$V_{CC} = 10.8$ V, $T_C = 25^\circ\text{C}$		50	mA
			$V_{CC} = 15$ V, $T_C = 25^\circ\text{C}$		80	
$f_{clock}$	Clock frequency, $T_A = 25^\circ\text{C}$			6.25	MHz	
$t_w$	Clock pulse duration, high or low, $T_A = 25^\circ\text{C}$	80			ns	
$t_{su}$	Setup time, data valid before clock $\uparrow$ , $T_A = 25^\circ\text{C}$	20			ns	
$t_h$	Hold time, data valid after clock $\uparrow$ , $T_A = 25^\circ\text{C}$	110			ns	
$T_A$	Operating free-air temperature	-55			°C	
$T_C$	Operating case temperature			125	°C	

**SN55551, SN55552**  
**ELECTROLUMINESCENT ROW DRIVER**

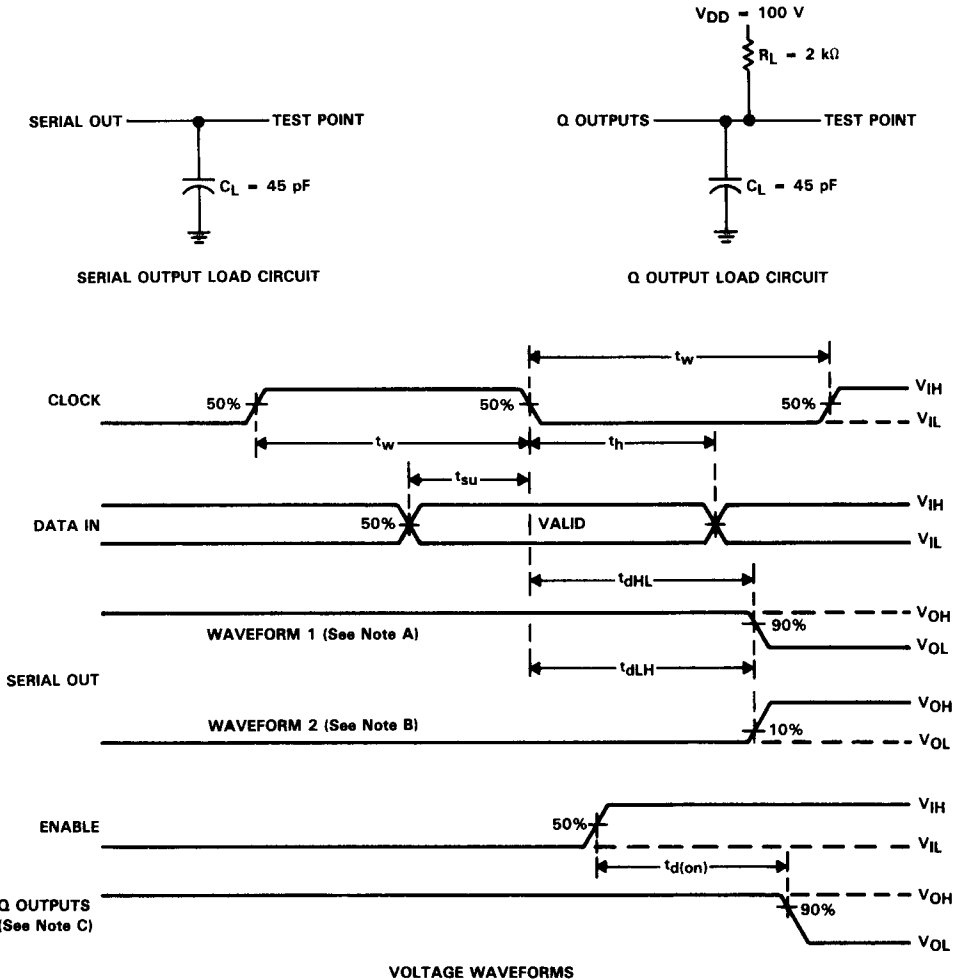
electrical characteristics over recommended operating temperature range,  $V_{CC} = 12\text{ V}$ , substrate common at 0 V

PARAMETER		TEST CONDITIONS	MIN	MAX	UNIT
$V_{OH}$	High-level output voltage	Serial outputs $I_O = -100\ \mu\text{A}$	10		V
$V_{OL}$	Low-level output voltage	Q outputs $I_O = 50\ \text{mA}$		50	V
		Serial output $I_O = 100\ \mu\text{A}$		1.5	
$I_{IH}$	High-level input current	$V_I = 12\ \text{V}$		5	$\mu\text{A}$
$I_{IL}$	Low-level input current	$V_I = 0$		-5	$\mu\text{A}$
$I_{O(off)}$	Off-state Q output current	$V_O = 200\ \text{V}$		50	$\mu\text{A}$
$I_{CC}$	Supply current			500	$\mu\text{A}$

switching characteristics,  $V_{CC} = 12\ \text{V}$ ,  $T_C = 25^\circ\text{C}$

PARAMETER		TEST CONDITIONS	MIN	MAX	UNIT
$t_{dLH}$	Delay time, clock $\downarrow$ to serial $\downarrow$	$C_L = 45\ \text{pF}$ to common, See Figure 1		200	ns
$t_{dHL}$	Delay time, clock $\downarrow$ to serial $\uparrow$			200	ns
$t_{dHL}$	Delay time, enable to Q output $\downarrow$	$V_{DD} = 100\ \text{V}$ , $R_L = 2\ \text{k}\Omega$ , $C_L = 45\ \text{pF}$ to common, See Figure 1		500	ns

**PARAMETER MEASUREMENT INFORMATION**

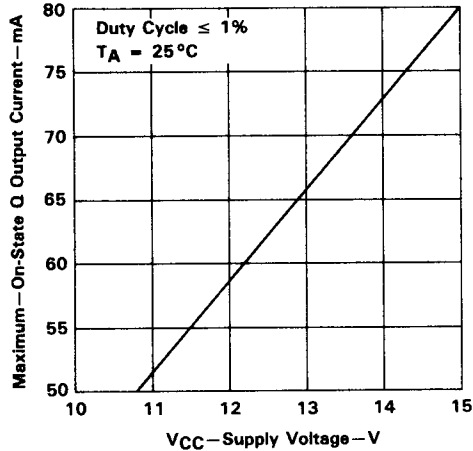


- NOTES: A. Waveform 1 is for internal conditions such that a low is clocked into R32.  
 B. Waveform 2 is for internal conditions such that a high is clocked into R32.  
 C. To measure  $t_{d(on)}$ , a high is stored in the associated register.

**FIGURE 1. SWITCHING CHARACTERISTICS**

**RECOMMENDED OPERATING CONDITIONS**

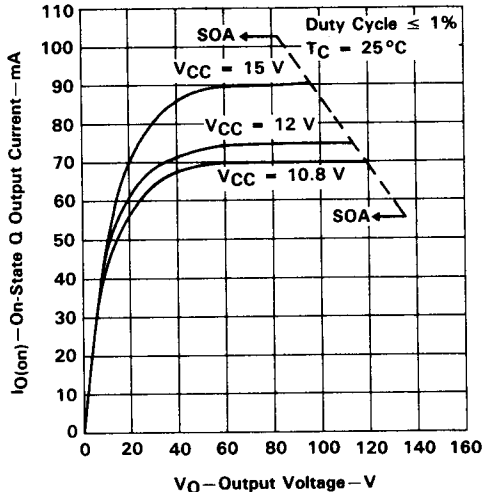
MAXIMUM ON-STATE Q OUTPUT CURRENT  
vs  
SUPPLY VOLTAGE



**FIGURE 2**

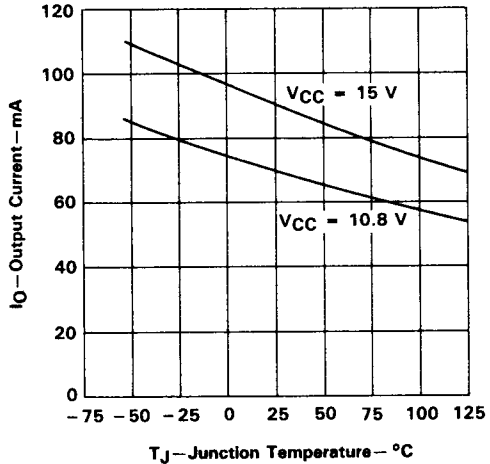
**TYPICAL CHARACTERISTICS**

OUTPUT CHARACTERISTICS SHOWING  
SAFE OPERATION AREA (SOA)



**FIGURE 3**

OUTPUT SATURATION CURRENT  
vs  
JUNCTION TEMPERATURE



**FIGURE 4**